## 11/27/

## IN THE STATES PATENT AND TRADEMA OFFICE REQ OR FILING APPLICATION UNDER 37 (1997), 1.53(b) WITHOUT FILING EE AND/OR WITHOUT EXECUTED INVENSOR'S DECLARATION

sistant Commissioner for Patents Chington, DC 20231

Facsimile: (703) 816-4100

HWB:ecb

Atty. Dkt. 925-219

Date: November 27, 2001

<u> </u>						
This is a request for filing a new PATENT APPLICATION under Rule 53(b) entitled:  METHOD FOR MANUFACTURING NONVOLATILE SEMICONDUCTOR MEMORY WITH NARROW VARIATION IN  THRESHOLD VOLTAGES OF MEMORY CELLS						
	Newly executed Decl pages of specification sheets of accompany Record the attached Attached is a Power of	rithout an executed inverted inverted inverted inverted inverted in the below identified inverted in the aration, Copy of Denie and claims (including ing drawing/s. assignment and return of Attorney.	ventor's oath/declar eventor(s). Attach eclaration from print of 4 numbered claim to the undersign foun Coun	aration.  led hereto are the following application, Abstraction, Abstraction, and  led.  led following foreign application	act ications: Day/Month/Year	
ទូនទ	2000-301132		Japa	lf I	28/11/2000	
Heart Start Stort Start can	, respectively, the entire content of which is hereby incorporated by reference in this application  Certified copy(ies) of foreign application(s) is/are attached.  Certified copy(ies) filed on  in prior application no.  filed					
	Please amend the specification by inserting the following paragraph before the first line:This application claims					
Hadi thu	the benefit of Provisional Application No. , filed , the entire content of which is hereby incorporated by					
	reference in this application Please amend the specification by inserting the following paragraph before the first line:This application is a					
######################################	which is hereby incorporated by reference in this application Petition filed in prior application to extend its life to insure co-pendency.					
	The prior application	is assigned to	•			
	It is hereby requested that the Examiner consider the art cited in the above parent application(s) by applicant and the Examiner for the reasons stated therein. A listing of that art is attached, but pursuant to Rule 98(d) copies are					
	not required.					
The state that then	Applicant claims "small entity" status.					
Also attached: Information Disclosure Statement; Information Request; Information Disclosure Statement; Information Request; Information Disclosure Statement deleting Inventor(s) named in prior application; Information Other:						
	Ammo Aoid Ocquen		tatement detetin	g inventor(s) nameu n	i prior application,	□ Otilej./
1.	Inventor:	Satoru		YAMAGATA	Jar	panese
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2.	Inventor:	Masanori		YOSHIMI	Jar	oanese
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(Zip Code)						
	See attached she	eet(s) for addition	onal invento	r(s) information!!	t	
Address all future communications to NIXON & VANDERHYE P.C., 1100 North Glebe Road, 8 <sup>th</sup> Floor, Arlington, VA 22201.						
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Arlington, Virginia 22201-4714 By Atty: H. Warren Burnam, Jr., Reg. No. 29,366 Telephone: (703) 816-4000						

Signature: Houra, Bure,